

INCHANGE Semiconductor

isc Product Specification

isc Silicon PNP Power Transistor

2SB1562

DESCRIPTION

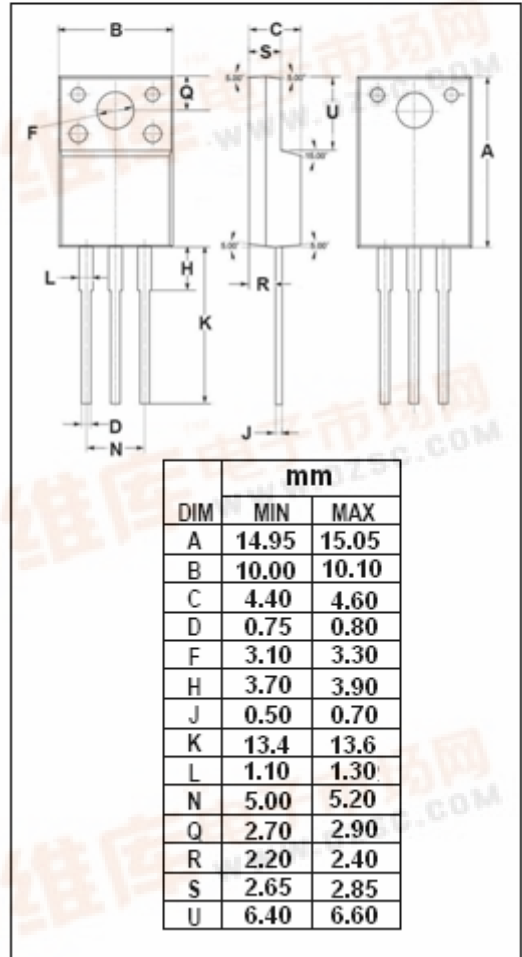
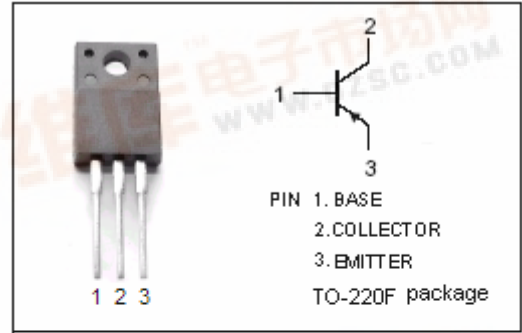
- High DC Current Gain-  
:  $h_{FE} = 300 \sim 1000 @ (V_{CE} = -5V, I_C = -0.5A)$
- Low Saturation Voltage-  
:  $V_{CE(sat)} = -0.5V(TYP.) @ (I_C = -2A, I_B = -20mA)$

APPLICATIONS

- Designed for power amplifier applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-7	V
$I_C$	Collector Current-Continuous	-3	A
$I_{CM}$	Collector Current-Pulse	-6	A
$I_B$	Base Current-Continuous	-0.6	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	25	W
	Collector Power Dissipation @ $T_a=25^\circ C$	2	
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-55~150	$^\circ C$



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## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA ; I <sub>B</sub> = 0	-60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -20mA		-0.5	-1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -5V		-0.7	-1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -60V ; I <sub>E</sub> =0			-100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -7V; I <sub>C</sub> =0			-100	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -5V	300		1000	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -2A ; V <sub>CE</sub> = -5V	100			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1.0MHz		60		pF